

# Programme: DT008 / 2 ELEK2108 Electronics 1 Laboratory Technical Report

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Collaborator 3:	-	-

Laboratory Number:	E
Semester Week Number:	10
Date:	25/03/2019

### **Submission Checklist and Declaration**

To ensure that the focus of the assessment of your laboratory report can include the development of higher order skills and competences associated with a Level 7 qualification, please complete the checklist and declaration below.

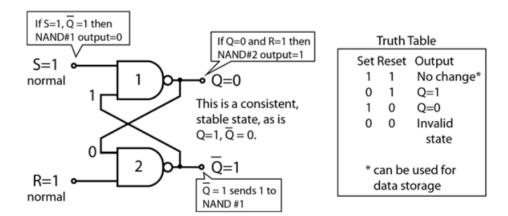
# I declare that the report that I am submitting: • is my original work, with secondary sources acknowledged; • was proofread thoroughly for typographical errors; • contains citations with references formatted in the IEEE citation style. I understand that my work can be returned uncorrected if the criteria are unfulfilled.

Signature:

### 1.0 Laboratory Aim

### • Describe the purpose of the laboratory or the research.

The Purpose of this lab was to create a memory NAND cell. This diagram that is shown below shows the states of the NAND cells and how they operate.

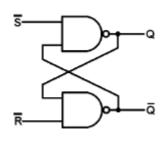


### 2.0 Laboratory Procedure

### Describe the actions taken during the work.

The NAND cell circuit contains 2 NAND gates connected together a pair of cross-coupled 2-inputs to simply make basic single bit set-rest SR flip-flop.

The Memory circuit functions by storing the voltage present on an input signal whenever they are triggered by a control signal and they keep store voltage until the next true state of the control (or trigger) signal.



Time		Time + 1
$\bar{\mathcal{S}}$	$ar{R}$	Q
0	0	1
0	1	1
1	0	0
1	1	NO CHANGE

If two inputs S and R of the NAND cell are active low (0) at the same time output Q goes high (1). If both inputs S and R of the NAND cell are high same time then the feedback loop can become unstable and the memory device can get temporary stuck in a stable region.

### 3.0 Results

• Present the results recorded from the investigation.

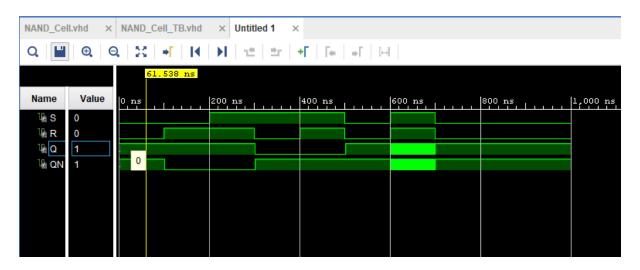


Figure 1 - Test simulator

NAND			
S	R	Q	QN
0	0	1	1
0	1	1	0
1	1	1	0
1	0	0	1

Operation	Waveform Timing (ns)
A set operation	200 ns
A reset operation	100 ns
A '0' being stored in memory	
A state where the Q and QN outputs are both	300 ns
driven to the same value	
A metastable state	700ns

Operation	Waveform Timing (ns)
A set operation	300 ns
A reset operation	500 ns
A '0' being stored in memory	300 ns
A state where the Q and QN outputs are both driven to the same value	500 ns
A metastable state	700 ns

## 4.0 Analysis

• Provide some comments that interpret what the results indicate or prove.

When S and R change their state, it changes the state of Q.

### 5.0 Conclusions

The result met the conditions, and the simulation reflected the design.

### 6.0 References

NAND cell diagram:

http://hyperphysics.phy-astr.gsu.edu/hbase/Electronic/ietron/nandlatch.png

NAND cells Research:

https://www.electronics-tutorials.ws/sequential/seq\_1.html

### **Submission Checklist**

1.	The cover page is appropriately complete.	$\boxtimes$
2.	The six sections in the body of the report are complete.	$\boxtimes$
3.	The constructive feedback from a collaborator is addressed.	$\boxtimes$
4.	A final spell-check is completed.	$\boxtimes$
5.	A backup copy of the report is online.	$\boxtimes$